

Page 2, line 36 to page 3, line 7:

Figs. 12A and 12B show results of an experiment in actual formation of devices. Fig. 11A shows those of devices in which device regions are not opposed whereas Fig. 12B shows those of devices in which device regions are opposed. This result shows that, in devices where device regions are not opposed, the withstand voltage property decreases to an unusable level when the STI width reaches 0.2 μ m, but in devices where device regions are opposed, they maintain a sufficient withstand voltage even under 0.2 μ m.

Page 4, lines 6-9:

forming a first well of a first conductivity and a second well of a second conductivity which is opposite to the first conductivity in a manner they are disposed adjacent to each other;

Page 6, lines 20-30:

As shown in Fig. 4, device regions 15 and 16 are partly opposed, but since their opposed extensions are not sufficiently wide, tapered angle does not increase sufficiently, and well isolation distance cannot be reduced sufficiently. To compensate it, a p^+ dummy region 19 is formed to extend from one side of the p^+ region 16 such that the n^+ region 15 is opposed with its full width. As a result, similarly to the configuration of Fig. 1, there exists a pattern of opposed device regions, and miniaturization of devices can be attained by using more miniaturized well isolation.

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If the concept of Embodiment 2 is used, opposed device regions need not be those actually used. That is, they may be dummy device regions. Fig. 5 shows an example of this concept, and a dummy pattern 20 is formed to confront the n^+ region 15. Note, however, that its width has to completely include the portion opposed to the width of the n^+ region 15. Therefore, if the dummy region has the width equal to the width of the n^+ region 15 as illustrated with the solid line, or a wider width as illustrated with the broken line, the requirement is satisfied.